Product Preview

256K x 16 Bit 3.3 V Asynchronous Fast Static RAM

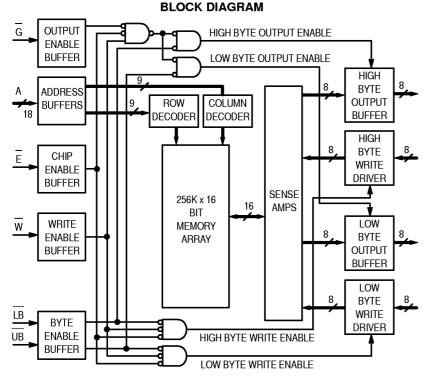
The MCM6943 is a 4,194,304 bit static random access memory organized as 262,144 words of 16 bits. Static design eliminates the need for external clocks or timing strobes.

The MCM6943 is equipped with chip enable (E), write enable (W), and output enable (G) pins, allowing for greater system flexibility and eliminating bus contention problems. Separate byte enable controls (LB and UB) allow individual bytes to be written and read. LB controls the lower bits DQ0 to DQ7, while UB controls the upper bits DQ8 to DQ15.

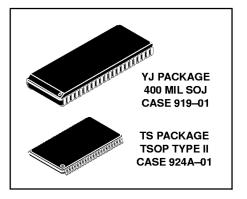
The MCM6943 is available in a 400 mil, 44-lead small-outline SOJ package and a 44-lead TSOP Type II package.

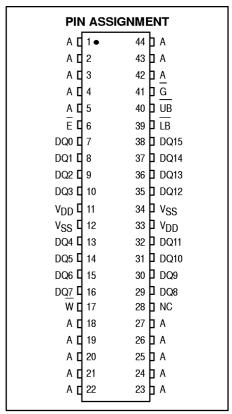
- Single 3.3 V ± 0.3 V Power Supply
- Fast Access Time: 8/10/12/15 ns
- Equal Address and Chip Enable Access Time
- All Inputs and Outputs are TTL Compatible
- Data Byte Control
- Fully Static Operation
- Power Operation: 265/250/240/230 mA Maximum, Active AC
- Standard Industrial Temperature Option: 40 to + 85°C
- Part Numbers (Standard Industrial Power): SCM6943YJ8A

SCM6943YJ10A SCM6943YJ12A SCM6943YJ15A



MCM6943





PIN NAMES
<u>A</u> 0 – A17 Address Input
<u>E</u> Chip Enable
<u>W</u> Write Enable
G Output Enable
<u>UB</u> Upper Byte
LB Lower Byte
DQ0 - DQ15 Data Input/Output
V _{DD} + 3.3 V Power Supply
V _{SS} Ground
NC No Connection

This document contains information on a product under development. Motorola reserves the right to change or discontinue this product without notice.

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TRUTH TABLE (X = Don't Care)

E	G	w	LB	UB	Mode	V _{DD} Current	DQ0 – DQ7	DQ8 – DQ15
Н	Х	Х	Х	Х	Not Selected	I _{SB1} , I _{SB2}	High-Z	High-Z
L	Н	Н	Х	Х	Output Disabled	I _{DDA}	I _{DDA} High–Z	
L	Х	Х	Н	Н	Output Disabled	I _{DDA}	High–Z	High-Z
L	L	Н	L	Н	Low Byte Read	I _{DDA}	D _{out}	High-Z
L	L	Н	Н	L	High Byte Read	I _{DDA}	High–Z	D _{out}
L	L	Н	L	L	Word Read	I _{DDA}	D _{out}	D _{out}
L	Х	L	L	Н	Low Byte Write	I _{DDA}	D _{in}	High-Z
L	Х	L	Н	L	High Byte Write	I _{DDA}	High-Z	D _{in}
L	Х	L	L	L	Word Write	IDDA	D _{in}	D _{in}

ABSOLUTE MAXIMUM RATINGS (See Notes)

Rating		Symbol	Value	Unit
Supply Voltage		V _{DD}	- 0.5 to + 4.6	V
Voltage on Any Pin		V _{in}	-0.5 to V _{DD} + 0.5	V
Output Current per Pin		l _{out}	± 20	mA
Package Power Dissipatio	n	PD	TBD	W
Temperature Under Bias	Commercial Industrial	T _{bias}	- 10 to + 85 - 45 to + 90	°C
Operating Temperature	Commercial Industrial	ТА	0 to + 70 - 45 to + 85	°C
Storage Temperature		T _{stg}	- 55 to + 150	°C

NOTES:

- Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPER-ATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.
- 2. All voltages are referenced to V_{SS} .
- 3. Power dissipation capability will be dependent upon package characteristics and use environment.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to these high impedance circuits.

This BiCMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow of at least 500 linear feet per minute is maintained.

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DC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{DD} = 3.3 V \pm 0.3 V, T_A = 0 to 70°C, Unless Otherwise Noted) $(T_A = -40 \text{ to} + 85^{\circ}\text{C for Industrial Temperature Offering})$

RECOMMENDED OPERATING CONDITIONS

Parameter		Min	Тур	Max	Unit
Power Supply Voltage	V _{DD}	3.0	3.3	3.6	V
Input High Voltage	VIH	2.2	_	V _{DD} + 0.3**	V
Input Low Voltage	V_{IL}	- 0.5*	_	0.8	٧

DC CHARACTERISTICS

Parameter		Symbol	Min	Max	Unit
Input Leakage Current (All Inputs, V _{in} = 0 to V _{DD})		llkg(l)	_	±1.0	μА
Output Leakage Current (E = V _{IH} , V _{out} = 0 to V _{DD})		lkg(O)	_	±1.0	μА
Output Low Voltage	$(I_{OL} = + 4.0 \text{ mA})$ $(I_{OL} = + 100 \mu\text{A})$	V _{OL}		0.4 V _{SS} + 0.2	V
Output High Voltage	$(I_{OH} = -4.0 \text{ mA})$ $(I_{OH} = -100 \mu\text{A})$	VOH	2.4 V _{DD} – 0.2		V

POWER SUPPLY CURRENTS

Parameter		Symbol	0 to 70°C	– 40 to + 85°C	Unit
AC Active Supply Current (Iout = 0 mA, V _{CC} = max)	MCM6943- 8: t _{AVAV} = 8 ns MCM6943-10: t _{AVAV} = 10 ns MCM6943-12: t _{AVAV} = 12 ns MCM6943-15: t _{AVAV} = 15 ns	Icc	265 250 240 230	275 260 250 240	mA
AC Standby Current (V _{CC} = max, E = V _{IH} , No other restrictions on other inputs)	MCM6943- 8: t _{AVAV} = 8 ns MCM6943-10: t _{AVAV} = 10 ns MCM6943-12: t _{AVAV} = 12 ns MCM6943-15: t _{AVAV} = 15 ns	I _{SB1}	55 50 50 45	60 55 55 50	mA
CMOS Standby Current ($E \ge V_{CC} - 0.2 \text{ V}, V_{in} \le (V_{CC} = \text{max}, f = 0 \text{ MHz})$	V _{SS} + 0.2 V or ≥ V _{CC} – 0.2 V)	I _{SB2}	5	5	mA

$\textbf{CAPACITANCE} \text{ (f = 1.0 MHz, dV = 3.0 V, } \\ T_{\mbox{\scriptsize A}} = 25^{\circ}\mbox{\scriptsize C}, \\ \mbox{Periodically Sampled Rather Than 100\% Tested)} \\$

Parameter	Symbol	Тур	Max	Unit
Address Input Capacitance	C _{in}	_	6	pF
Control Input Capacitance	C _{in}	_	6	pF
Input/Output Capacitance	C _{I/O}	_	8	pF

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 $^{^*}V_{JL} \ (min) = -0.5 \ V \ dc; \ V_{JL} \ (min) = -2.0 \ V \ ac \ (pulse \ width \le 20 \ ns) \ for \ I \le 20.0 \ mA.$ $^{**}V_{JH} \ (max) = V_{DD} + 0.3 \ V \ dc; \ V_{JH} \ (max) = V_{DD} + 2.0 \ V \ ac \ (pulse \ width \le 20 \ ns) \ for \ I \le 20.0 \ mA.$

AC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{CC} = 3.3 V \pm 0.3 V, T_A = 0 to + 70° C, Unless Otherwise Noted) (T_A = -40 to + 85° C for Industrial Temperature Offering)

Logic Input Timing Measurement Reference Level 1.50 V	Output Timing Reference Level
Logic Input Pulse Levels 0 to 3.0 V	Output Load See Figure 1a
Input Rise/Fall Time	

READ CYCLE TIMING (See Notes 1 and 2)

		MCM6943-8 MCM6943-10 M		MCM6943-12		MCM6943-15					
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Read Cycle Time	[†] AVAV	8		10	_	12	_	15	_	ns	3
Address Access Time	[†] AVQV	_	8	_	10	_	12	_	15	ns	
Enable Access Time	^t ELQV	_	8	_	10	_	12	_	15	ns	4
Output Enable Access Time	^t GLQV	_	4	_	5	_	6	_	7	ns	
Output Hold from Address Change	^t AXQX	3		3	_	3	_	3	_	ns	
Enable Low to Output Active	^t ELQX	3		3	_	3	_	3	_	ns	5, 6, 7
Output Enable Low to Output Active	^t GLQX	0		0	_	0	_	0	_	ns	5, 6, 7
Enable High to Output High–Z	^t EHQZ	0	4	0	5	0	6	0	7	ns	5, 6, 7
Output Enable High to Output High-Z	^t GHQZ	0	4	0	5	0	6	0	7	ns	5, 6, 7
Byte Enable Access Time	^t BLQV	_	4	_	5	_	6	_	7	ns	
Byte Enable Low to Output Active	^t BLQX	0		0	_	0	_	0	_	ns	5, 6, 7
Byte High to Output High-Z	^t BHQZ	0	4	0	5	0	6	0	7	ns	5, 6, 7

NOTES:

- 1. W is high for read cycle.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. All read cycle timings are referenced from the last valid address to the first transitioning address.
- 4. Addresses valid prior to or coincident with E going low.
- 5. At any given voltage and temperature, t_{EHQZ} max < t_{ELQX} min, and t_{GHQZ} max < t_{GLQX} min, both for a given device and from device to device.
- 6. Transition is measured \pm 200 mV from steady-state voltage with load of Figure 1b.
- 7. This parameter is sampled and not 100% tested.
- 8. Device is continuously selected ($E \le V_{IL}$, $G \le V_{IL}$).

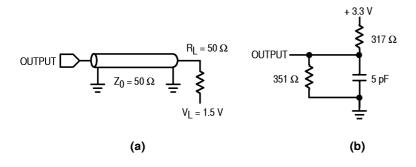


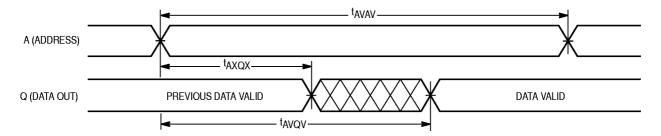
Figure 1. AC Test Loads

TIMING LIMITS

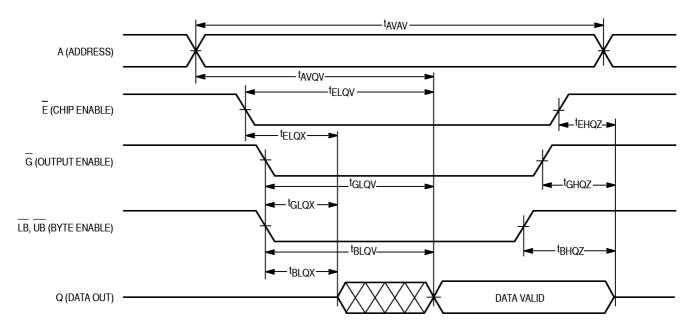
The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time. On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

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READ CYCLE 1 (See Note 8)



READ CYCLE 2 (See Note 4)



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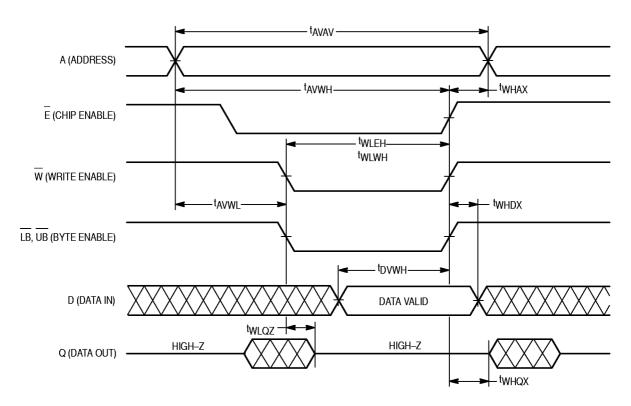
WRITE CYCLE 1 (W Controlled; See Notes 1, 2, and 3)

		MCM6943-8		МСМ6	943–10	МСМ6	943–12	MCM6943-15			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	[†] AVAV	8	_	10	_	12	_	15	_	ns	4
Address Setup Time	†AVWL	0	_	0	_	0	_	0	_	ns	
Address Valid to End of Write	^t AVWH	8	_	9	_	10	_	12	_	ns	
Address Valid to End of Write (G High)	^t AVWH	7	_	8	_	9	_	10	_	ns	
Write Pulse Width	tWLWH tWLEH	8	_	9	_	10	_	12	_	ns	
Write Pulse Width (G High)	tWLWH tWLEH	7	_	8	_	9	_	10	_	ns	
Data Valid to End of Write	^t DVWH	4	_	5	_	6	_	7	_	ns	
Data Hold Time	twhdx	0	_	0	_	0	_	0	_	ns	
Write Low to Data High–Z	tWLQZ	0	4	0	5	0	6	0	7	ns	5, 6, 7
Write High to Output Active	tWHQX	3	_	3	_	3	_	3	_	ns	5, 6, 7
Write Recovery Time	tWHAX	0	_	0	_	0	_	0	_	ns	

NOTES:

- 1. A write occurs during the overlap of E low and W low.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. If G goes low coincident with or after W goes low, the output will remain in a high-impedance state.
- 4. All write cycle timings are referenced from the last valid address to the first transitioning address.
- 5. Transition is measured \pm 200 mV from steady–state voltage with load of Figure 1b.
- 6. This parameter is sampled and not 100% tested.
- 7. At any given voltage and temperature, twLoz max < twHox min both for a given device and from device to device.

__ WRITE CYCLE 1 (W Controlled; See Notes 1, 2, and 3)



MCM6943 MOTOROLA FAST SRAM

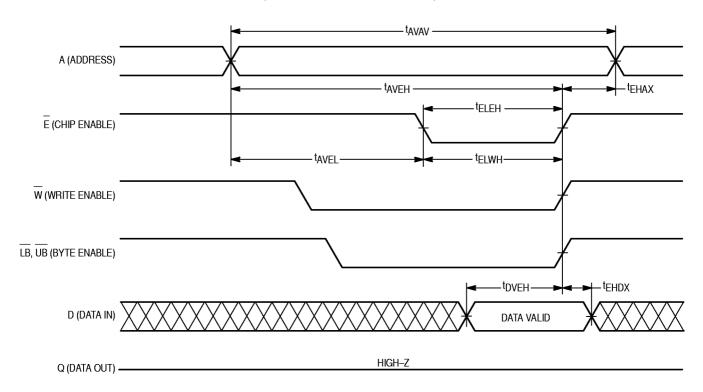
WRITE CYCLE 2 (E Controlled; See Notes 1, 2, and 3)

		MCM6943-8		мсм6	943–10	MCM6943-12		MCM6943-15			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	[†] AVAV	8	_	10	_	12	_	15	_	ns	4
Address Setup Time	^t AVEL	0	_	0	_	0	_	0	_	ns	
Address Valid to End of Write	[†] AVEH	8	_	9	_	10	_	12	_	ns	
Address Valid to End of Write (G High)	[†] AVEH	7	_	8	_	9	_	10	_	ns	
Enable to End of Write	tELEH, tELWH	8	_	9	_	10	_	12	_	ns	5, 6
Enable to End of Write (G High)	tELEH, tELWH	7	_	8	_	9	_	10	_	ns	5, 6
Data Valid to End of Write	^t DVEH	4		5	_	6	_	7	_	ns	
Data Hold Time	^t EHDX	0	_	0	_	0	_	0	_	ns	
Write Recovery Time	^t EHAX	0	_	0	_	0	_	0	_	ns	

NOTES:

- 1. A write occurs during the overlap of \overline{E} low and \overline{W} low.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. If G goes low coincident with or after W goes low, the output will remain in a high-impedance state.
- 4. All write cycle timing is referenced from the last valid address to the first transitioning address.
- 5. If <u>E</u> goes low coincident with or after <u>W</u> goes low, the output will remain in a high impedance condition.
- 6. If E goes high coincident with or before W goes high, the output will remain in a high impedance condition.

WRITE CYCLE 2 (E Controlled; See Notes 1, 2, and 3)



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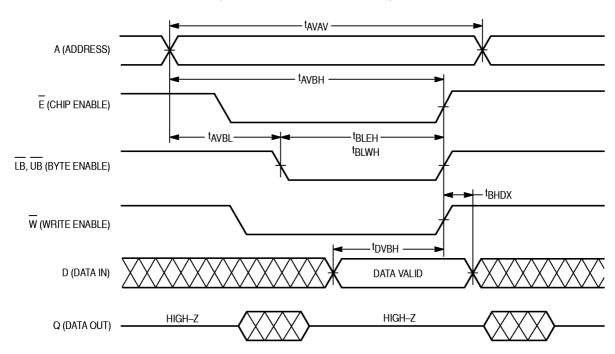
WRITE CYCLE 3 (E Controlled; See Notes 1, 2, and 3)

		мсм6	MCM6943-8		943–10	MCM6943-12		MCM6943-15			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	[†] AVAV	8	_	10	_	12	_	15	_	ns	4
Address Setup Time	^t AVBL	0	_	0	_	0	_	0	_	ns	
Address Valid to End of Write	^t AVBH	8	_	9	_	10	_	12	_	ns	
Address Valid to End of Write (G High)	^t AVBH	7	_	8	_	9	_	10		ns	
Byte Pulse Width	^t BLWH ^t BLEH	8	_	9	_	10	_	12	_	ns	
Byte Pulse Width (G High)	^t BLWH ^t BLEH	7	_	8	_	9	_	10	_	ns	
Data Valid to End of Write	^t DVBH	4	_	5	_	6	_	7	_	ns	
Data Hold Time	^t BHDX	0	_	0	_	0	_	0	_	ns	

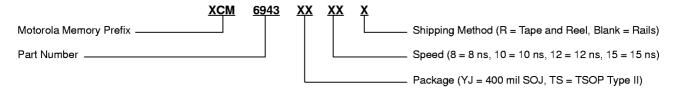
NOTES:

- 1. A write occurs during the overlap of E low and W low.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. If G goes low coincident with or after W goes low, the output will remain in a high-impedance state.
- 4. All write cycle timings are referenced from the last valid address to the first transitioning address.

__ WRITE CYCLE 3 (E Controlled; See Notes 1, 2, and 3)



ORDERING INFORMATION (Order by Full Part Number)



Full Commercial Part Numbers — MCM6943YJ8 MCM6943YJ8R MCM6943TS8 MCM6943YJ10 MCM6943YJ10R MCM6943YJ12R MCM6943YJ12R MCM6943YJ15R MCM6943TS15

Full Industrial Part Numbers — SCM6943YJ8A SCM6943YJ8AR SCM6943TS10A3 SCM6943YJ10AR SCM6943TS10A3 SCM6943YJ10AR SCM6943TS10A3 SCM6943YJ10AR SCM6943TS10A3 SCM6943TS10A3 SCM6943YJ10AR SCM6943TS10A3 SCM6943TS10A3

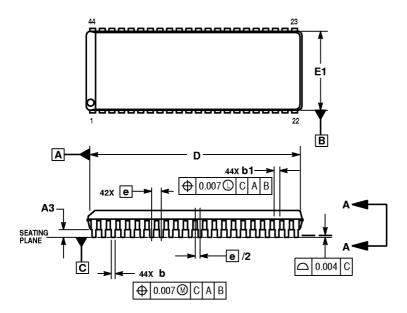
SCM6943YJ10A SCM6943YJ10AR SCM6943TS10A* SCM6943YJ12A SCM6943YJ12AR SCM6943TS12A* SCM6943YJ15A SCM6943YJ15AR SCM6943TS15A*

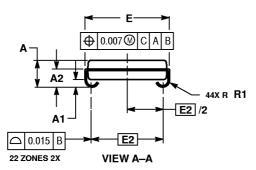
MOTOROLA FAST SRAM MCM6943

^{*} Not available in Tape and Reel.

PACKAGE DIMENSIONS

YJ PACKAGE 44-LEAD 400 MIL SOJ CASE 919-01





NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: INCH.

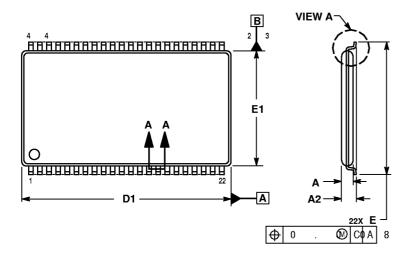
 3. DIMENSION D DOES NOT INCLUDE MOLD FLASH, TIE BAR BURRS AND GATE BURRS. MOLD FLASH, TIE BAR BURRS AND GATE BURRS SHALL NO INTERLEAD FLASH SHALL NOT EXCEED 0.010 PER SIDE.
- NI EHLEAD FLASH SHALL NOT EACED 0.010
 PER SIDE.

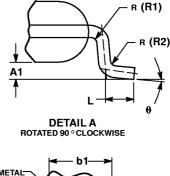
 4. THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM. DIMENSIONS D AND E1 AND, HENCE, DATUMS A AND B, ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY EXCLUSIVE OF MOLD FLASH, TIE BAR BURBS, GATE BURBS AND INTELEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.

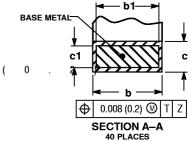
 5. DIMENSION 15 DOES NOT INCLUDE DAWBAR PROTRUSION OR INTRUSION. THE DAMBAR PROTRUSION(S) SHALL NOT CAUSE THE SHOULDER WIDTH TO EXCEED 10 MAX BY MORE THAN 0.005. THE DAMBAR INTRUSION(S) SHALL NOT REDUCE THE SHOULDER WIDTH TO LESS THAN 0.001 BELOW 15 MIN.

	INCHES		
DIM	MIN MAX		
Α	0.128	0.148	
A 1	0.025		
A 2	0.082		
A 3	0.035	0.045	
а	0.015	0.020	
b1	0.026	0.032	
D	1.120	1.130	
ш	0.435	0.445	
E1	0.395	0.405	
E2	0.370 BSC		
е	0.050 BSC		
R1	0.030	0.040	

TS PACKAGE 44-LEAD **TSOP TYPE II** CASE 924A-01







0.004 (0.1) C **Чинининининининини** 4x e /2 ---Ċ

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH
- DIMENSION D1 AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE MOLD PROTRUSION IS 0.006 (0.015) PER SIDE.
 DIMENSION 6 DOES NOT INCLUDE DAMBAR
- PROTRUSIONS. DAMBAR PROTRUSIONS SHALL NOT ALLOW THE 6 DIMENSION TO EXCEED 0.023 (0.58).

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α		0.050		1.270
A 1	0.002	0.006	0.051	0.152
A2	0.038	0.042	0.965	1.067
g	0.012	0.018	0.305	0.457
b1	0.012	0.016	0.305	0.406
U	0.005	0.008	0.127	0.203
cī	0.004	0.006	0.101	0.152
Ď	0.721	0.729	18.313	18.517
е	0.0315 BSC		0.800 BSC	
Е	0.456	0.470	11.582	11.938
Ξ	0.396	0.404	10.058	10.262
۲	0.016	0.023	0.406	0.584
R1	0.004 REF		0.100 REF	
R2	0.004 REF		0.100 REF	
θ	0 °	5°	0°	5°

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